

Schottky Barrier Diode

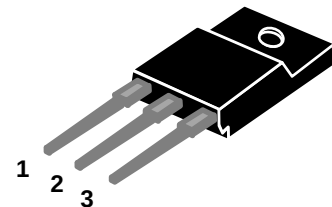
Features

- High Breakdown Voltage ($V_{RRM} = 200V$)
- Low Forward Voltage Drop
- Low Leakage Current

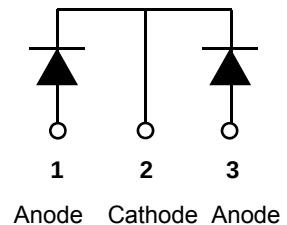
Application

- Rectifiers for Switch Mode Power Supplies (SMPS)
- Power Inverter and Converter

TO-220F-3P Package



Pin Configuration



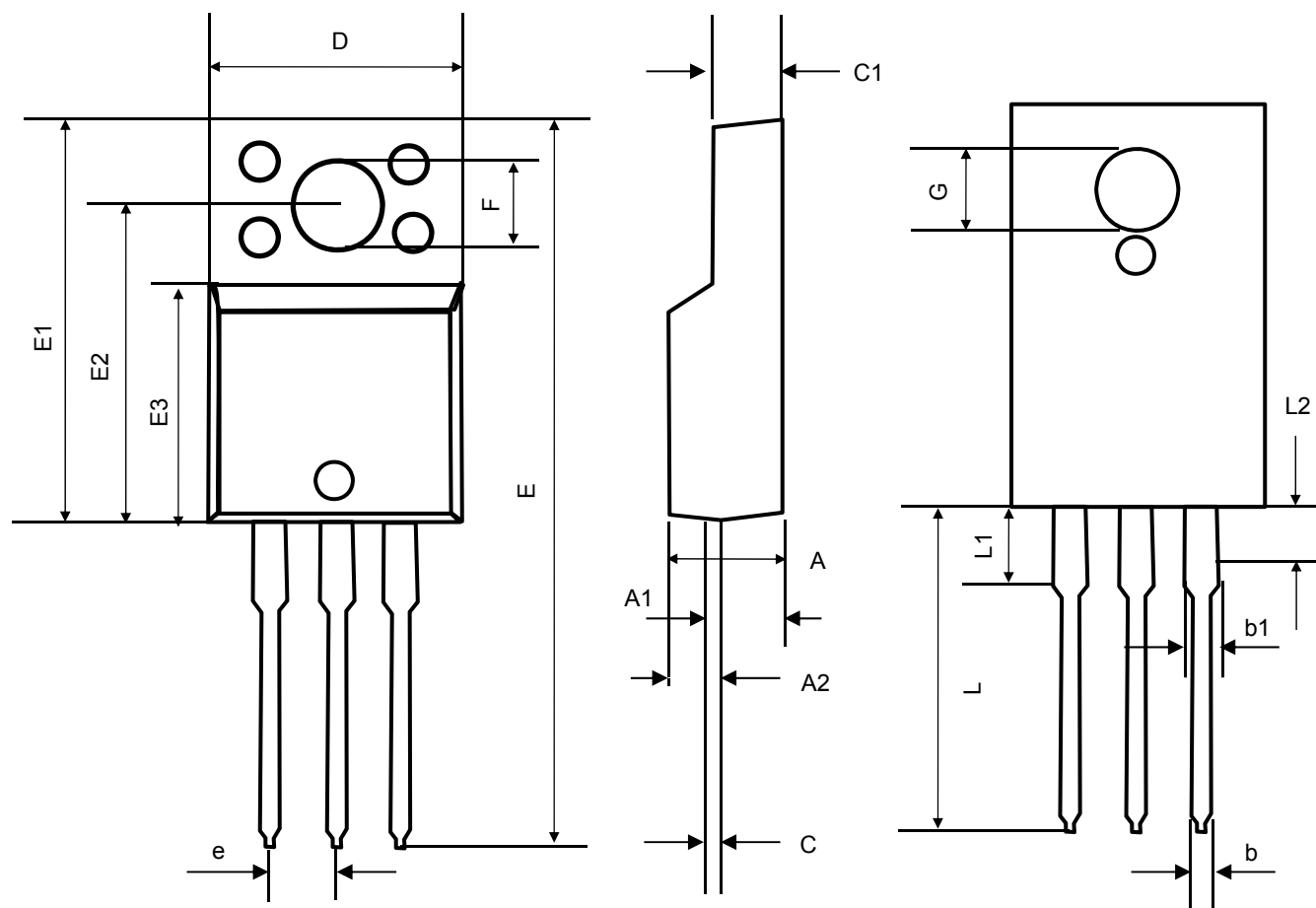
Absolute Maximum Rating ($T_a = 25^\circ C$)

Parameter		Symbol	Value	Unit
Maximum Repetitive Reverse Voltage		V_{RM}	200	V
Maximum Average Forward Rectified Current	Per diode	$I_{F(AV)}$	5	A
	Total diode		10	
Forward Current Surge Peak		I_{FSM}	120	A
Junction Temperature		T_J	150	$^\circ C$
Storage Temperature		T_{STG}	-45 ~ 150	$^\circ C$

Electrical Characteristics (Per diode, $T_a = 25^\circ C$)

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Forward Voltage	V_{FM}	$I_{FM} = 5A$	-	0.85	0.95	V
Reverse Leakage Current	I_{RM}	$V_{RM} = 200V$	-	-	10	μA
Junction Capacitance	C_j	$V_R = 1V_{DC}, f=1MHz$	-	150	-	pF

Package Outline Drawing: TO-220F-3P



SYMBOL	MILLIMETER			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	-	-	4.60	
A1	2.45	2.50	2.55	
A2	1.95	2.00	2.05	
b	0.65	0.75	0.85	
b1	1.07	1.27	1.47	
C	0.40	0.50	0.60	
C1	2.70	2.80	2.90	
D	9.90	10.00	10.10	
E	28.00	-	28.60	
E1	15.50	15.60	15.70	
E2	12.30	12.40	12.50	
E3	9.15	9.20	9.25	
F	3.30	3.40	3.50	
G	3.10	3.20	3.30	
e1	5.08 BSC			
L	12.40	-	13.00	
L1	3.46 BSC			
L2	2.21 BSC			